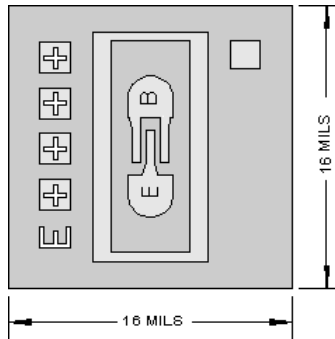


**Chip Type 2C918**  
**Geometry 0013**  
**Polarity NPN**

**Generic Packaged Parts:**  
**2N918**



[Request Quotation](#)

Chip type **2C918** by Semicoa Semiconductors provides performance similar to these devices.

**Product Summary:**

**APPLICATIONS:** Designed for high frequency oscillator, multiplier and driver applications.

**Part Numbers:**

2N918, 2N918UB, SD918, SD918F, SQ918, SQ918F

**Features:**

- High frequency rating

Mechanical Specifications		
Metallization	Top	Al - 15 kÅ min.
	Backside	Au - 6.5 kÅ nom.
Bonding Pad Size	Emitter	2.7 mils x 2.7 mils
	Base	2.7 mils x 2.7 mils
Die Thickness	8 mils nominal	
Chip Area	16 mils x 16 mils	
Top Surface	Silox Passivated	

Electrical Characteristics				
$T_A = 25^\circ\text{C}$				
Parameter	Test conditions	Min	Max	Unit
$BV_{CEO}$	$I_C = 3.0 \text{ mA}, I_B = 0$	15	---	V dc
$BV_{CBO}$	$I_C = 10 \mu\text{A}, I_E = 0$	30	---	V dc
$BV_{EBO}$	$I_E = 10 \mu\text{A}, I_C = 0$	3.0	---	V dc
$I_{CBO}$	$V_{CB} = 15 \text{ V}, I_E = 0$	---	10	nA
$h_{FE}$	$I_C = 3.0 \text{ mA dc}, V_{CE} = 1.0 \text{ V}$	20	---	---
$V_{CE(sat)}$	$I_C = 30 \text{ mA dc}, I_B = 3.0 \text{ mA}$	---	0.3	V dc

*Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300  $\mu\text{s}$ , duty cycle less than 2%.*